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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICATION OF: Wolfgang Clemens et al.
SERIAL NO: Not assigned GROUP ART UNIT: Not assigned
FILED: Herewith EXAMINER: Not assigned
CUSTOMER NO.: 27162
FOR: Organic Electronic Component With High-Resolution Structuring
And Process For The Production Thereof

ATTY/DKT NO.: 415000-128

Commissioner for Patents
P.O. Box 1450
Alexandria VA 22313-1450

SIR:

Pursuant to 37 C.F.R. §1.56(a), Applicant(s) hereby cite(s) the enclosed documents listed on the attached copy of Form PTO-1449 which are believed to be material to the patentability of the above-identified application.

This Information Disclosure Statement is filed in accordance with the paragraph of 37 CFR §1.97 indicated below:

- ☒ §1.97(b) This Information Disclosure Statement is filed:
- (1) Within three months of the filing date of a national application; OR
 - (2) Within three months of the date of entry of the national stage of an international application; OR
 - (3) Before the mailing of a first Office Action on the merits.
No fee or statement is required.

☐ §1.97(c) This Information Disclosure Statement is filed after the period specified in paragraph (b) above, but before the mailing date of either:

- (1) A Final Action or under 37 CFR §1.113; OR
- (2) A Notice of Allowance under 37 CFR §1.311; AND

is accompanied by either: (check one)

- ☐ The statement as specified in 37 CFR §1.97(e) set out below; OR
- ☐ The fee of \$180.00 under 37 CFR §1.17(p).

____ §1.97(d) This Information Disclosure Statement is filed after the mailing date of either:

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BUT filed on or before payment of the Issue Fee; AND
is accompanied by:

- (1) The statement as specified in 37 CFR §1.97(e) as set forth below; AND
- (2) Petition is hereby made under 37 CFR §1.97(d) for consideration of this Information Disclosure Statement; AND,
- (3) The petition fee of \$180.00 set out in 37 CFR §1.17(i).

____ §1.97(e) The undersigned Attorney hereby states that:

____ each item of information contained in this Information Disclosure Statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing date of this Information Disclosure Statement;

or

____ no item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application, or to the knowledge of the undersigned Attorney after making reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing date of the Information Disclosure Statement.

This Information Disclosure Statement provides a detailed list of the references cited in various pending applications listed in applicant's Disclosure Statement filed herewith.

The Commissioner is authorized to charge payment of any fees associated with this communication or credit any overpayment to Deposit Account No. 03-0678.

Respectfully submitted,
Wolfgang Clemens et al.


William Squire
Reg. No. 25,378
CARELLA, BYRNE BAIN, GILFILLAN,
CECCHI, STEWART & OLSTEIN
5 Becker Farm Road
Roseland, NJ 07068
Tel: (973)994-1700
Fax: (973)994-1744

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>				Complete if Known	
				Application Number	Not assigned
				Filing Date	Herewith
				First Named Inventor	Wolfgang Clemens
				Group Art Unit	Not assigned
Examiner Name	Not assigned				
Sheet	1	Of	7	Attorney Docket Number	411000-128

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		ZANGARA L: "Metall Statt Halbleiter, Programmierung Von Embedded ROMS Ueber Die Metallisierungen", Elektronik, Franzis Verlag GMBH, Munchen, DE, Bd. 47, Nr. 16, 4 August 1998 (1998-08-04), Seiten 52-55, XP000847917, ISSN: 0013-5658, Seite 52, rechtes Plate, Zeile 7-Seite 53, linke Spalte, Zeile 14; Abbildungen 1, 2	
		ZHENG, Xiang-Yang et al., "Electrochemical Patterning of the Surface of Insulators with Electrically Conductive Polymers", J. Electrochem. Soc., v. 142, 1995, pp L226-L227.	X
		ZIE VOOR TITEL BOEK, de 2e PAGINA, XP-002189001, PG 196-228.	X

Examiner Signature		Date Considered	
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10/533756
JC17 Rec'd PCT/PTO 03 MAY 2005

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICATION OF: Wolfgang Clemens et al.
SERIAL NO: Not assigned GROUP ART UNIT: Not assigned
FILED: Herewith EXAMINER: Not assigned
CUSTOMER NO.: 27162
FOR: Organic Electronic Component With High-Resolution Structuring
And Process For The Production Thereof
ATTY/DKT NO.: 411000-128

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

DISCLOSURE STATEMENT UNDER 37 CFR 1.56

SIR:

This paper is to bring to the attention of the PTO the following U.S. pending applications, all of which are related in different respects to organic electronic devices and/or method of making such devices such as transistors, diodes, integrated circuits and the like. Many of these applications also may have one or more common inventors.

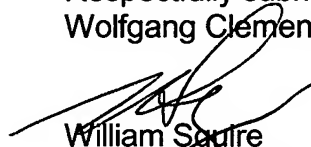
<u>Application No.</u>	<u>Title</u>	<u>Inventors</u>	<u>Atty. Dkt. No.</u>
10/332,140	Method for the Production and Configuration of Organic Field-Effect Transistors (OFET)	Adolf Bernds et al.	411000-103
10/344,951	Organic Field-Effect Transistor (OFET), A Production Method Therefor, An Integrated Circuit Constructed From the Same and Their Uses	Adolf Bernds et al.	411000-99

<u>Application No.</u>	<u>Title</u>	<u>Inventors</u>	<u>Atty. Dkt. No.</u>
10/362,932	Organic Field Effect Transistor, Method for Structuring an OFET and Integrated Circuit	Adolf Bernds et al	411000-110
10/380,113	Organic Rectifier, Circuit, RFID Tag and Use of an Organic Rectifier	Adolf Bernds et al.	411000-106
10/380,206	Organic Memory, Identification Marker (RFID-TAG) with Organic Memory and Uses of an Organic Memory	Adolf Bernds et al.	411000-102
10/381,032	Electrode and/or Conductor Track for Organic Components and Production Method Thereof	Adolf Bernds et al.	411000-105
10/433,959	Organic Field Effect Transistor, Method For Structuring an OFET and Integrated Circuit	Adolf Bernds	411000-108
10/433,961	Device For Detecting and/or Transmitting at Least One Environmental Influence, Method for Producing Said Device and Use Thereof	Wolfgang Clemens et al.	411000-111
10/467,636	Organic Field Effect Transistor With a Photostructured Gate Dielectric, Method for the Production and Use Thereof in Organic Electronics	Adolf Bernds et al.	411000-104
10/473,050	Device With At Least Two Organic Electronic Components and Method for Producing the Same	Adolf Bernds et al.	411000-113
10/479,234	Organic Field Effect Transistor, Method for Production and Use Thereof in the Assembly of Integrated Circuits	Adolf Bernds et al.	411000-101
10/479,238	Method For Producing Conductive Structures by Means of Printing Technique, and Active Components Produced Therefrom For Integrated Circuits	Adolf Bernds et al.	411000-100
10/492,922	Insulator for An Organic Electronic Component	Erwann Guillet et al.	411000-115
10/492,923	Electronic Unit, Circuit Design for the Same and Production Method	Wolfgang Clemens et al.	411000-114
10/498,610	Organic Field Effect Transistor with Offset Threshold Voltage and the Use Thereof	Walter Fix et al.	411000-119

<u>Application No.</u>	<u>Title</u>	<u>Inventors</u>	<u>Atty. Dkt. No.</u>
10/508,640	Logic Component Comprising Organic Field Effect Transistors	Walter Fix et al.	411000-120
10/508,737	Device and Method for Laser Structuring Functional Polymers and the Uses Thereof	Adolf Bernds et al.	411000-121
10/517,750	Substrate for an Organic Field Effect Transistor, Use of the Substrate, Method of Increasing the Charge Carrier Mobility and Organic Field Effect Transistor (OFET)	Wolfgang Clemens et a.	411000-122
10/523,216	Electronic Component Comprising Predominantly Organic Functional Materials and a Process for the Production Thereof	Adolf Bernds et al.	411000-123
10/523,487	Electronic Device	Wolfgang Clemens et al.	411000-124
10/524,646	Organic Component For Overvoltage Protection And Associated Circuit	Walter Fix et al.	411000-127

The Commissioner is authorized to charge payment of any fees associated with this communication or credit any overpayment to Deposit Account No. 03-0678.

Respectfully submitted,
Wolfgang Clemens et al.



William Squire
Reg. No. 25,378
CARELLA, BYRNE, BAIN, GILFILLAN,
CECCHI, STEWART & OLSTEIN
5 Becker Farm Road
Roseland, NJ 07068
Tel: (973)994-1700
Fax: (973)994-1744

Substitute for form 1449A/PTO				Complete if Known Application Number: Not assigned Filing Date: Herewith First Named Inventor: Wolfgang Clemens Group Art Unit: Not assigned Examiner Name: Not assigned Attorney Docket Number: 411000-128	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)					
Sheet	1	Of	1		

U.S. PATENT DOCUMENTS					
Examiner Initial*	Cite No. ¹	Document Number Number-Kid Code ² (if known)	Publication- Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	1	US-6,852,583	10/09/2003	Adolf Bernds et al.	See Disclosure Statement filed herewith
	2	US-10/344,951	N/A	Adolf Bernds et al.	
	3	US-10./362,932	10/02/2003	Adolf Bernds et al.	
	4	US-10/380,113	09/25/2003	Adolf Bernds et al.	
	5	US-10/380,206	N/A	Adolf Bernds et al.	
	6	US-10/381,032	N/A	Adolf Bernds et al.	
	7	US-10/433,959	N/A	Adolf Bernds	
	8	US-10/433,961	N/A	Wolfgang Clemens et al.	
	9	US-10/451,108	N/A	Mark Giles et al.	
	10	US-10/467,636	N/A	Adolf Bernds et al.	
	11	US-10/473,050	N/A	Adolf Bernds et al.	
	12	US-10/479,234	12/30/2004	Adolf Bernds et al.	
	13	US-10/479,238	N/A	Adolf Bernds et al.	
	14	US-10/492,922	N/A	Erwann Buillet et al.	
	15	US-10/492,923	12/23/2004	Wolfgang Clemens et al.	
	16	US-10/498,610	N/A	Walter Fix et al.	
	17	US-10/508,640	N/A	Walter Fix et al.	
	18	US-10/508,737	N/A	Adolf Bernds et al.	
	19	US-10/517,750	N/A	Wolfgang Clemens et al.	
	20	US-10/523,216	N/A	Adolf Bernds et al.	
	21	US-10/523,487	N/A	Wolfgang Clemens et al.	
	22	US-10/524,646	N/A	Walter Fix et al.	
Examiner Signature			Date Considered		

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